

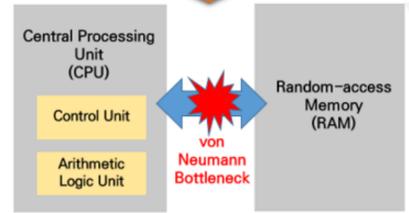
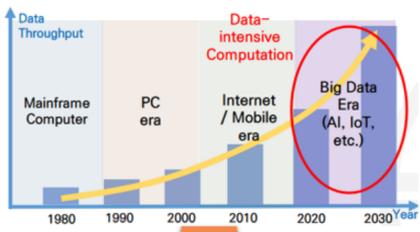
In-Memory Nearest Neighbor Search with Nanoelectromechanical Ternary Content-Addressable Memory

이재성 (삼차원 집적 및 소자 연구실)

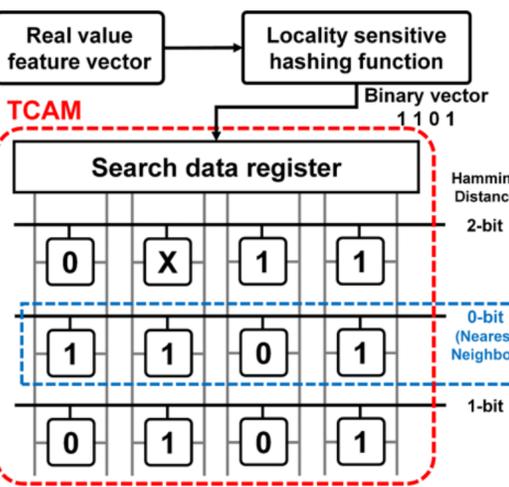
SOGANG UNIVERSITY

Motivation

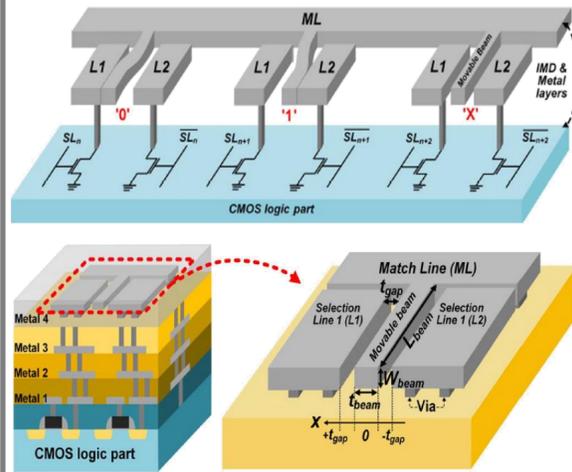
Limitation of conventional CPU-based Nearest Neighbor search



Ternary content-addressable memory-based Nearest Neighbor search method



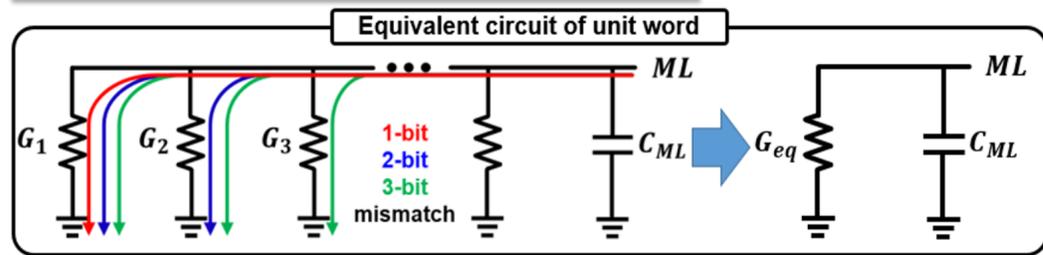
Ideas



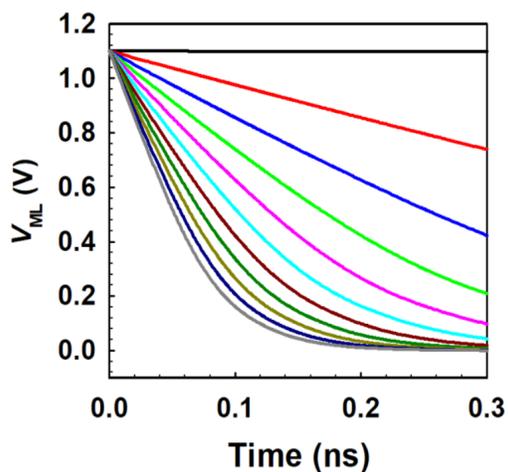
<J.S.Lee and W.Y.Choi, IEEE TED, 2021>

- NEMTCAM has been considered as a promising option of nonvolatile TCAM designs.
- NEMTCAM achieves the smallest cell area, highest speed, energy efficiency among other TCAM design.
- In this study, NEMTCAM was introduced as a novel NN classifier in memory-augmented neural network.

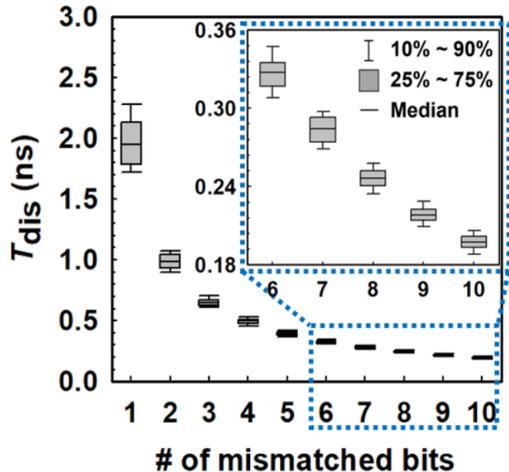
Simulation Result



Simulated ML voltage increasing with the number of mismatched bits

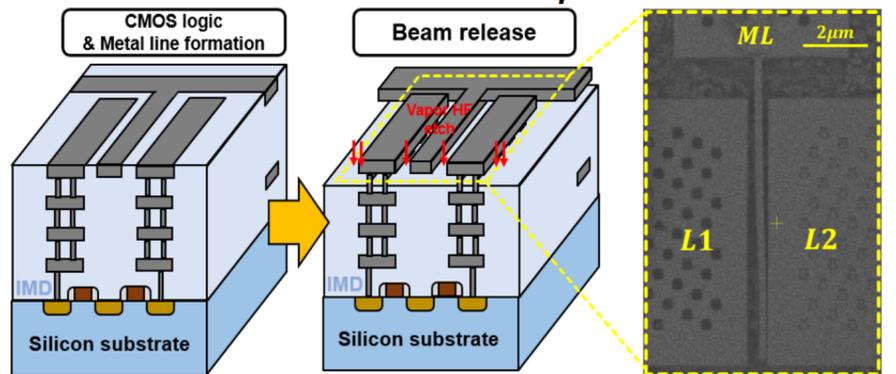


Calculated discharge delay (T_dis) with the effect of device-to-device variations

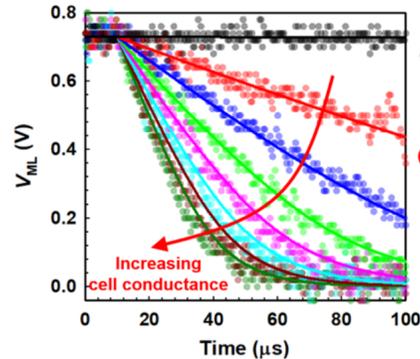


Experimental Result

NEMTCAM fabrication process

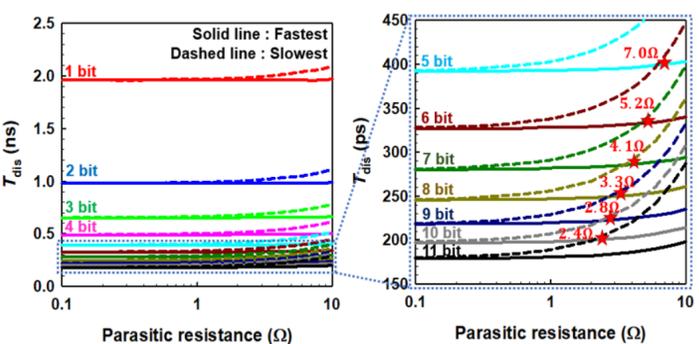
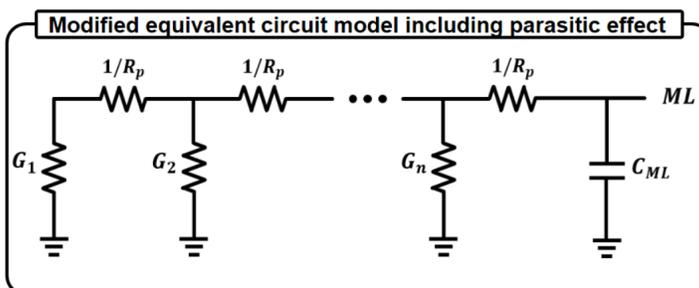


Measurement result



- NEM memory switches are patterned using a dual damascene process.
- IMD layer was selectively removed using vapor HF and fluorine-based plasma etch process.
- It was observed that a higher conductance led to a faster ML voltage drop.

Parasitic Resistance Effect



Analytic model analysis

- Total conductance (G_{eq}) can be calculated as follows:

$$G_{eq} \approx \frac{\sum_{i=1}^n G_i}{1 + \sum_{i=1}^n i G_i R_p} \quad (R_p G_i \ll 1)$$
- G_{eq} 's when T_{dis} can be the smallest and the largest are derived as follows:

$$G_{eq,fastest}(k) = \frac{2k G_{miss}}{2+k(k+1)R_p G_{miss}}$$

$$G_{eq,slowest}(k) = \frac{2k G_{miss}}{2+k(2n-k+1)R_p G_{miss}}$$
- To avoid the overlap between k -bit and $(k+1)$ -bit mismatched case, the following condition should be satisfied:

$$G_{eq,fastest}(k) < G_{eq,slowest}(k+1)$$
- As a result, the condition of R_p is derived as follows:

$$R_p < \frac{2R_{miss}}{k(k+1)(2n-2k-1)}$$

Analysis

- NEMTCAM using the 65-nm node can discriminate up to 10 Hamming distance in a 32-bit word, which is applicable to generic NN search.
- For higher accuracy, when a larger bit-width is needed, G_{miss} can be decreased.

Conclusion

- An in-memory NN search operation using the NEMTCAM was successfully confirmed by both simulations and experiments.
- This will enable next-generation CAM architectures to transcend the existing neural network system.